AOS Semiconductor
Product Reliability Report

AO4726/AO4726L, rev A

Plastic Encapsulated Device

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This AOS product reliability report summarizes the qualification result for AO4726. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4726 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AO4726 uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a low side FET in SMPS, load switching and general purpose applications.

Absolute Maximum Ratings T_A=25°C unless otherwise noted					
Parameter		**Symbol**	**10 sec**	**Steady state**	**Units**
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	±12		V
Continuous Drain Current	T_A=25°C	I_{DSM}	18	13	A
	T_A=70°C		14	10	
Pulsed Drain Current		I_{DM}	80		
Avalanche Current		I_{AR}	42		A
Repetitive avalanche energy L=0.3mH		E_{AR}	265		mJ
Power Dissipation	T_A=25°C	P_{DSM}	3.1	1.7	W
	T_A=70°C		2.0	1.1	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics					
Parameter		**Symbol**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient	T ≤ 10s	$R_{\theta JA}$	32	40	°C/W
Maximum Junction-to-Ambient	Steady-State		60	75	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	17	24	°C/W

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II. Die / Package Information:

	AO4726	AO4726L (Green Compound)
Process	Standard sub-micron Low voltage N channel process	Standard sub-micron Low voltage N channel process
Package Type	8 leads SOIC	8 leads SOIC
Lead Frame	Cu, S/pad, Ag spot	Cu, S/pad, Ag spot
Die Attach	Ag epoxy	Ag epoxy
Bond wire	S: Cu 2mils, G: Au 1.3mils	S: Cu 2mils, G: Au 1.3mils
Mold Material	Epoxy resin with silica filler	Epoxy resin with silica filler
Filler % (Spherical/Flake)	90/10	100/0
Flammability Rating	UL-94 V-0	UL-94 V-0
Backside Metallization	Ti / Ni / Ag	Ti / Ni / Ag
Moisture Level	Up to Level 1 *	Up to Level 1*

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO4726 (Standard) & AO4726L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	**Standard: 1hr PCT+3 cycle reflow@260°c Green: 168hr 85°c /85%RH +3 cycles reflow@260°c**	**0hr**	**Standard: 83 lots Green: 29 lots**	**17380 pcs**	**0**
HTGB	**Temp = 150°c , Vgs=100% of Vgsmax**	**168 / 500 hrs 1000 hrs**	**3 lots (Note A*)**	**246 pcs 77+5 pcs / lot**	**0**
HTRB	**Temp = 150°c , Vds=80% of Vdsmax**	**168 / 500 hrs 1000 hrs**	**3 lots (Note A*)**	**246 pcs 77+5 pcs / lot**	**0**
HAST	**130 +/- 2°c , 85%RH, 33.3 psi, Vgs = 80% of Vgs max**	**100 hrs**	**Standard: 81 lots Green: 16 lots (Note B**)**	**5335 pcs 50+5 pcs / lot**	**0**
Pressure Pot	**121°c , 29.7 psi , 100%RH**	**96 hrs**	**Standard: 83 lots Green: 20 lots (Note B**)**	**5665 pcs 50+5 pcs / lot**	**0**
Temperature Cycle	**-65°c to 150°c , air to air**	**250 / 500 cycles**	**Standard: 87 lots Green: 29 lots (Note B**)**	**6380 pcs 50+5 pcs / lot**	**0**

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III. Result of Reliability Stress for AO4726 (Standard) & AO4726L (Green) Continues

DPA	**Internal Vision** **Cross-section** **X-ray**	**NA**	**5** **5** **5**	**5** **5** **5**	**0**
CSAM		**NA**	**5**	**5**	**0**
Bond Integrity	**Room Temp** **150°c bake** **150°c bake**	**0hr** **250hr** **500hr**	**40** **40** **40**	**40 wires** **40 wires** **40 wires**	**0**
Solderability	**245°c**	**5 sec**	**15**	**15 leads**	**0**

Note A: The HTGB and HTRB reliability data presents total of available AO4726 and AO4726L burn-in data up to the published date.
Note B: The pressure pot, temperature cycle and HAST reliability data for AO4726 and AO4726L comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion): 43
MTTF =2654 years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).
The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4726). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9$ **/ [**2 (N) (H) (Af)**]** = 1.83×10^9 / **[**2 (3 x 164) (168) (258)**]** = 43
MTTF = 10^9 / FIT =2.32×10^7hrs = 2654 years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval
N = Total Number of units from HTRB and HTGB tests
H = Duration of HTRB/HTGB testing
Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)
Acceleration Factor [**Af**] = **Exp** [Ea / **k** (1/Tj u – 1/Tj s)]
Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16
Tj u =The use junction temperature in degree (Kelvin), K = C+273.16
k = Boltzmann's constant, 8.617164×10^{-5}eV / K

V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual.
Guaranteed Outgoing Defect Rate: **< 25 ppm**
Quality Sample Plan: conform to **Mil-Std-105D**